2SA2167

FOR HIGH CURRENT DRIVE APPLICATION
SILICON PNP EPITAXIAL TYPE

DESCRIPTION

2SA2167 is a silicon PNP epitaxial type transistor. It is designed with high voltage, high Collector current, high Collector dissipation.

FEATURE

High voltage VcEo=-60V

High Collector current Ic=-2A

Low Collector to Emitter saturation voltage

VcE(sat) = 0.5VMax (@Ic=-1A/IB=-50mA)

High Collector dissipation PC=500mW

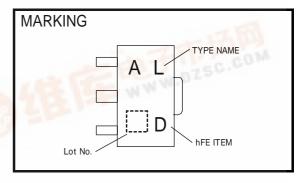
APPLICATION

Audiovisual apparatus, VTR, Relay drive

MAXIMUM RATINGS (Ta=25

Parameter	Ratings	Unit
Collector to Base voltage	-60	V
Emitter to Base voltage	-6	V
Collector to Emitter voltage	-60	V
Collector current	-2	Α
Peak Collector current	-3	Α
Collector dissipation	500	mW
Junction temperature	150	97
Storage temperature	-55 ~ 150	
	Collector to Base voltage Emitter to Base voltage Collector to Emitter voltage Collector current Peak Collector current Collector dissipation Junction temperature	Collector to Base voltage -60 Emitter to Base voltage -6 Collector to Emitter voltage -60 Collector current -2 Peak Collector current -3 Collector dissipation 500 Junction temperature 150

OUTLINE DRAWING Unit:mm 4.6MAX 1.5 0.53 0.48MAX MARKING TERMINAL CONNECTOR : BASE : EMITTER : COLLECTOR JEITA: SC-62 JEDEC: SOT-89



ELECTRICAL CHARACTERISTICS (Ta=25

Symbol	Parameter	Test condition	Limits		Unit	
Symbol			Min	Тур	Max	Offic
V(BR)CBO	Collector to Base brake down voltage	IC=-10uA、IE=0mA	-60		7.77	V
V(BR)EBO	Emitter to Base brake down voltage	IE=-10uA、IC=0mA	-6	0.00	Ten.	V
V(BR)CEO	Collector to Emitter brake down voltage	IC=-2mA、RBE=	-60			V
Ісво	Collector cut off current	VCB=-50V, IE=0mA			-0.2	μΑ
ІЕВО	Emitter cut off current	VEB=-4V、IC=0mA			-0.2	μΑ
hfe	DC forward current gain	VCE=-4V、IC=-100mA	55		300	-
VCE(sat)	Collector to Emitter saturation voltage	IC=-1A、IB=-50mA		-0.2	-0.5	V
fT	Gain band width product	VCE=-2V、IE=10mA		65		MHz
Cob	Collector output capacitance	VCB=10V、IE=0mA、f=1MHz		23		pF

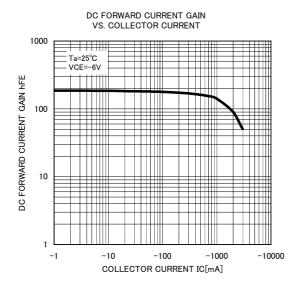
MARKING	С	D	Е
hFE	55 ~ 110	90 ~ 180	150 ~ 300

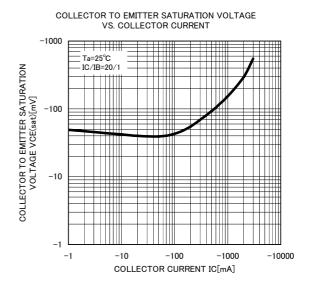


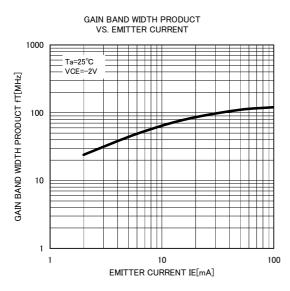
2SA2167

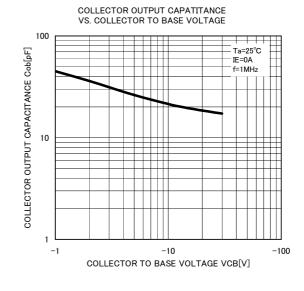
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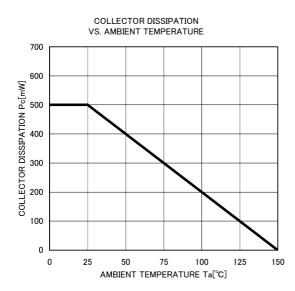
TYPICAL CHARACTERISTICS













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